0.5 Amp Output Current IGBT Gate Drive Optocoupler

Technical Data

Features

- 0.5 A Minimum Peak Output Current
- 15 kV/µs Minimum Common Mode Rejection (CMR) at V_{CM} = 1500 V
- 1.0 V Maximum Low Level Output Voltage (V_{OL})
 Eliminates Need for Negative Gate Drive
- $I_{CC} = 5$ mA Maximum Supply Current
- Under Voltage Lock-Out Protection (UVLO) with Hysteresis
- Wide Operating V_{CC} Range: 15 to 30 Volts
- 0.5 µs Maximum Propagation Delay
- +/- 0.35 µs Maximum Delay Between Devices/Channels
- Industrial Temperature Range:
 - -40°C to 100°C
- HCPL-315J: Channel One to Channel Two Output Isolation = 1500 Vrms/1 min.
- Safety and Regulatory Approval:

UL Recognized (UL1577) 3750 Vrms/1 min.

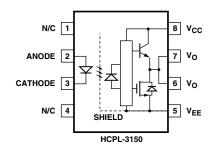
IEC/EN/DIN EN 60747-5-2 Approved

$$\begin{split} &V_{IORM} = 630 \ V_{peak} \\ &(HCPL\text{-}3150 \ Option \ 060 \ only) \\ &V_{IORM} = 891 \ V_{peak} \ (HCPL\text{-}\\ &315J) \ CSA \ Certified \end{split}$$

Applications

- Isolated IGBT/MOSFET Gate Drive
- AC and Brushless DC Motor Drives
- Industrial Inverters
- Switch Mode Power Supplies (SMPS)
- Uninterruptable Power Supplies (UPS)

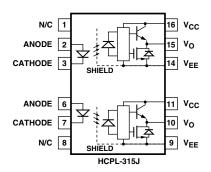
Functional Diagram



HCPL-3150 (Single Channel) HCPL-315J (Dual Channel)

Description

The HCPL-315X consists of a LED optically coupled to an integrated circuit with a power output stage. This optocoupler is ideally suited for driving power IGBTs and MOSFETs used in motor control inverter applications. The high operating voltage range of the output stage provides the drive voltages required by gate controlled devices. The voltage and current supplied by this optocoupler makes it ideally suited for directly driving IGBTs with ratings up to 1200 V/50 A. For IGBTs with higher ratings, the HCPL-3150/315J can be used to drive a discrete power stage which drives the IGBT gate.



TRUTH TABLE

LED	V _{CC} - V _{EE} "Positive Going" (i.e., Turn-On)	V _{CC} - V _{EE} "Negative-Going" (i.e., Turn-Off)	V _o
OFF	0 - 30 V	0 - 30 V	LOW
ON	0 - 11 V	0 - 9.5 V	LOW
ON	11 - 13.5 V	9.5 - 12 V	TRANSITION
ON	13.5 - 30 V	12 - 30 V	HIGH

A 0.1 μ F bypass capacitor must be connected between the V_{CC} and V_{EE} pins for each channel.

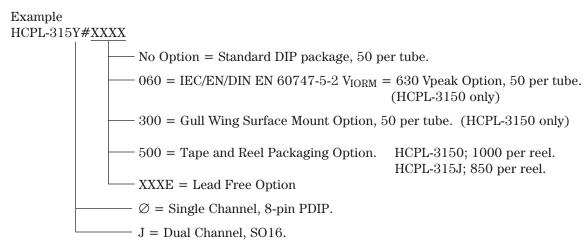
CAUTION: It is advised that normal static precautions be taken in handling and assembly of this component to prevent damage and/or degradation which may be induced by ESD.

Selection Guide: Invertor Gate Drive Optoisolators

Package Type		8-Pin Dl	IP (300 mil)		Widebody (400 mil)	Sm	-16			
Part Number	HCPL-3150	HCPL-3120	HCPL-J312	HCPL-J314	HCNW-3120	HCPL-315J	HCPL-316J	HCPL-314J		
Number of Channels	1	1	1	1	1	2	1	2		
IEC/EN/DIN EN 60747-5-2 Approvals	V _{IO} 630 ' Option	RM V _{peak} n 060	V _{I0} 891	$\begin{array}{c cccc} V_{IORM} & V_{IORM} & V_{IORM} \\ 891V_{peak} & 1414\ V_{peak} & 891\ V_p \end{array}$			${V_{\rm IORM} \atop 891~V_{\rm peak}}$			
UL Approval	37 Vrms/			750 71 min.	5000 Vrms/1min.		3750 Vrms/1 min.			
Output Peak Current	0.5A	2A	2A	0.4A	2A	0.5A	2A	0.4A		
CMR (minimum)		15 kV/μs		10 kV/μs		15 kV/μs		10 kV/μs		
UVLO		Yes		No		Yes		No		
Fault Status			No				Yes	No		

Ordering Information

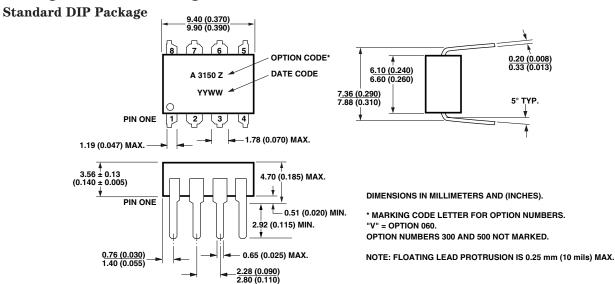
Specify Part Number followed by Option Number (if desired)



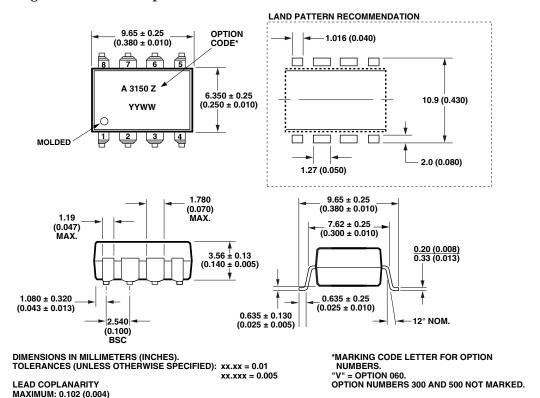
Option data sheets available. Contact Agilent sales representative or authorized distributor.

Remarks: The notation "#" is used for existing products, while (new) products launched since 15th July 2001 and lead free option will use "-"

Package Outline Drawings

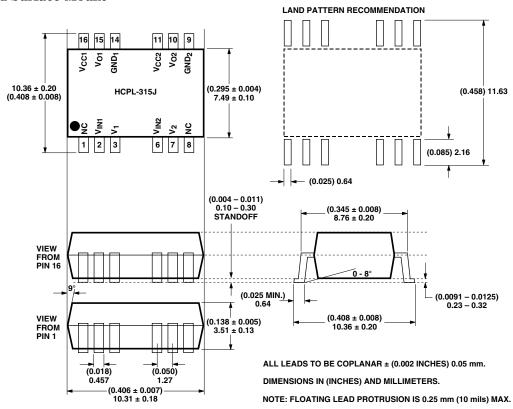


Package Outline Drawings Gull-Wing Surface-Mount Option 300

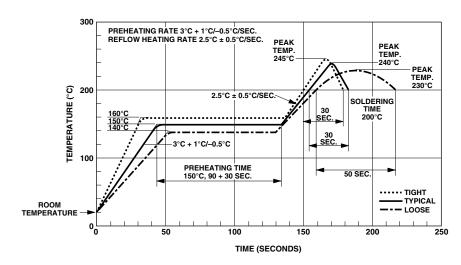


NOTE: FLOATING LEAD PROTRUSION IS 0.25 mm (10 mils) MAX.

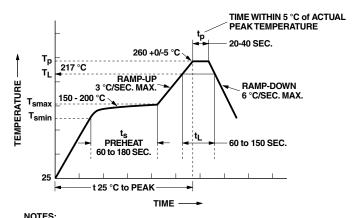
16 - Lead Surface Mount



Solder Reflow Thermal Profile



Recommended Pb-Free IR Profile



THE TIME FROM 25 °C to PEAK TEMPERATURE = 8 MINUTES MAX. T_{smax} = 200 °C, T_{smin} = 150 °C

Regulatory Information

The HCPL-3150 and HCPL-315J have been approved by the following organizations:

\mathbf{UL}

Recognized under UL 1577, Component Recognition Program, File E55361.

CSA

Approved under CSA Component Acceptance Notice #5, File CA 88324.

IEC/EN/DIN EN 60747-5-2

Approved under: IEC 60747-5-2:1997 + A1:2002 EN 60747-5-2:2001 + A1:2002 DIN EN 60747-5-2 (VDE 0884 Teil 2):2003-01. (Option 060 and HCPL-315J only)

IEC/EN/DIN EN 60747-5-2 Insulation Characteristics

Description	Symbol	HCPL-3150#060	HCPL-315J**	Unit
Installation classification per DIN VDE				
0110/1.89, Table 1			T T\$7	
for rated mains voltage ≤ 150 Vrms for rated mains voltage ≤ 300 Vrms		I-IV	I-IV I-III	
for rated mains voltage ≤ 500 Vrms		I-III	I-III I-II	
Climatic Classification		55/100/21	55/100/21	
Pollution Degree (DIN VDE 0110/1.89)		2	2	
Maximum Working Insulation Voltage	V _{IORM}	630	891	Vpeak
$\label{eq:local_local_problem} \begin{split} & \text{Input to Output Test Voltage, Method b*} \\ & V_{\text{IORM}} \ge 1.875 = V_{PR}, 100\% \text{Production} \\ & \text{Test with } t_m = 1 \text{sec,} \\ & \text{Partial discharge} < 5 \text{pC} \end{split}$	V_{PR}	1181	1670	Vpeak
$\label{eq:local_local_local_local_local} \begin{split} & \text{Input to Output Test Voltage, Method a*} \\ & V_{\text{IORM}} x 1.5 = V_{PR}, \text{Type and Sample} \\ & \text{Test, t}_m = 60 \text{sec,} \\ & \text{Partial discharge} < 5 \text{pC} \end{split}$	$ m V_{PR}$	945	1336	Vpeak
Highest Allowable Overvoltage* (Transient Overvoltage t _{ini} = 10 sec)	V _{IOTM}	6000	6000	Vpeak
Safety-Limiting Values – Maximum Values Allowed in the Event of a Failure, Also See Figure 37, Thermal Derating Curve.				
Case Temperature	T_{S}	175	175	°C
Input Current	Is, input	230	400	mA
Output Power	Ps, output	600	1200	mW
Insulation Resistance at T_S , $V_{IO} = 500 \text{ V}$	R_{S}	$\geq 10^9$	$\geq 10^9$	Ω

^{**}Approval Pending.

Note: Isolation characteristics are guaranteed only within the safety maximum ratings which must be ensured by protective circuits in application.

^{*}Refer to the front of the optocoupler section of the current Catalog, under Product Safety Regulations section IEC/EN/DIN EN 60747-5-2, for a detailed description of Method a and Method b partial discharge test profiles.

Insulation and Safety Related Specifications

Parameter	Symbol	HCPL-3150	HCPL-315J	Units	Conditions
Minimum External	L(101)	7.1	8.3	mm	Measured from input terminals
Air Gap					to output terminals, shortest
(External Clearance)					distance through air.
Minimum External	L(102)	7.4	8.3	mm	Measured from input terminals
Tracking					to output erminals, shortest
(External Creepage)					distance path along body.
Minimum Internal		0.08	≥ 0.5	mm	Through insulation distance
Plastic Gap					conductor to conductor.
(Internal Clearance)					
Tracking Resistance	CTI	≥ 175	≥ 175	Volts	DIN IEC 112/VDE 0303 Part 1
(Comparative Tracking					
Index)					
Isolation Group		IIIa	IIIa		Material Group (DIN VDE 0110,
					1/89, Table 1)

Option 300 - surface mount classification is Class A in accordance with CECC 00802.

Absolute Maximum Ratings

Parameter	Symbol	Min.	Max.	Units	Note
Storage Temperature	T_{S}	-55	125	$^{\circ}\!\mathrm{C}$	
Operating Temperature	T _A	-40	100	$^{\circ}$ C	
Average Input Current	I _{F(AVG)}		25	mA	1, 16
Peak Transient Input Current (<1 µs pulse width, 300 pps)	I _{F(TRAN)}		1.0	A	
Reverse Input Voltage	$V_{ m R}$		5	Volts	
"High" Peak Output Current	I _{OH(PEAK)}		0.6	A	2, 16
"Low" Peak Output Current	I _{OL(PEAK)}		0.6	A	2, 16
Supply Voltage	$(V_{\rm CC}$ - $V_{\rm EE})$	0	35	Volts	
Output Voltage	V _{O(PEAK)}	0	$V_{\rm CC}$	Volts	
Output Power Dissipation	Po		250	mW	3, 16
Total Power Dissipation	P_{T}		295	mW	4, 16
Lead Solder Temperature	260°C for 10 sec., 1.6 mm below seating plane				
Solder Reflow Temperature Profile	See	Package Ou	tline Drawin	gs Section	

Recommended Operating Conditions

Parameter	Symbol	Min.	Max.	Units
Power Supply Voltage	$(V_{CC} - V_{EE})$	15	30	Volts
Input Current (ON)	$I_{F(ON)}$	7	16	mA
Input Voltage (OFF)	$V_{F(OFF)}$	-3.0	0.8	V
Operating Temperature	T_{A}	-40	100	$^{\circ}\mathrm{C}$

Electrical Specifications (DC)

Over recommended operating conditions (T_A = -40 to 100°C, $I_{F(ON)}$ = 7 to 16 mA, $V_{F(OFF)}$ = -3.0 to 0.8 V, V_{CC} = 15 to 30 V, V_{EE} = Ground, each channel) unless otherwise specified.

$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Parameter	Symbol	Min.	Typ.*	Max.	Units	Test Condi	tions	Fig.	Note
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	High Level	I _{OH}	0.1	0.4		A	$V_{\rm O} = (V_{\rm CC} - 4)$	1 V)	2, 3,	5
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Output Current		0.5				$V_{\rm O} = (V_{\rm CC} - 15 \text{ V})$		17	2
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Low Level	I_{OL}	0.1	0.6		A	$V_{\rm O} = (V_{\rm EE} +$	2.5 V)	5, 6,	5
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Output Current		0.5]	$V_{\rm O} = (V_{\rm EE} +$	15 V)	18	2
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	-	V _{OH}	(V _{CC} - 4)	(V _{CC} - 3)		V	$I_{\rm O} = -100 \; {\rm m}$	A		6, 7
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		V _{OL}		0.4	1.0	V	$I_{\rm O} = 100 \text{mA}$			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	•	I _{CCH}		2.5	5.0	mA		,	7, 8	16
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		I_{CCL}		2.7	5.0	mA		,		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Threshold Input	I_{FLH}		2.2	5.0	mA	HCPL-3150	$I_O = 0 \text{ mA},$	9, 15,	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Current Low to High		,	2.6	6.4		HCPL-315J	$V_{\rm O} > 5 \text{ V}$	21	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	_	V_{FHL}	0.8			V				
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Input Forward Voltage	V_{F}	1.2	1.5	1.8	V	HCPL-3150	$I_F = 10 \text{ mA}$	16	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				1.6	1.95	1	HCPL-315J			
Breakdown Voltage 3 HCPL-315J $I_R = 10 \mu A$ Input Capacitance C_{IN} 70 pF $f = 1 \text{ MHz}, V_F = 0 \text{ V}$ UVLO Threshold V_{UVLO+} 11.0 12.3 13.5 V $V_O > 5 \text{ V},$ 22, V_{UVLO-} 9.5 10.7 12.0 $I_F = 10 \text{ mA}$ 36	Coefficient of	$\Delta V_F/\Delta T_A$		-1.6		mV/°C	$I_{\rm F} = 10 \text{ mA}$			
	-	BV_R	5			V	HCPL-3150	$I_R = 10 \mu A$		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Breakdown Voltage		3				HCPL-315J	$I_R = 10 \mu A$		
V_{UVLO} 9.5 10.7 12.0 $I_F = 10 \text{ mA}$ 36	Input Capacitance	C_{IN}		70		pF	$f = 1 \text{ MHz}, V_1$	F = 0 V		
707E0- 0.0 10.1 12.0 1F 10 Har	UVLO Threshold	V _{UVLO+}	11.0	12.3	13.5	V	$V_0 > 5 V$,		22,	
1777 0 177		V _{UVLO} -	9.5	10.7	12.0]	$I_F = 10 \text{ mA}$		36	
UVLO Hysteresis UVLO _{HYS} 1.6 V	UVLO Hysteresis	UVLO _{HYS}		1.6		V				

^{*}All typical values at $T_A=25\,^{\circ}\!\text{C}$ and V_{CC} - $V_{EE}=\overline{30}$ V, unless otherwise noted.

Switching Specifications (AC)

Over recommended operating conditions (T_A = -40 to 100°C, $I_{F(ON)}$ = 7 to 16 mA, $V_{F(OFF)}$ = -3.0 to 0.8 V, V_{CC} = 15 to 30 V, V_{EE} = Ground, each channel) unless otherwise specified.

Parameter	Symbol	Min.	Typ.*	Max.	Units	Test Conditions	Fig.	Note
Propagation Delay	${ m t_{PLH}}$	0.10	0.30	0.50	μs	$Rg = 47 \Omega,$	10, 11,	14
Time to High						Cg = 3 nF,	12, 13,	
Output Level						f = 10 kHz,	14, 23	
						Duty Cycle = 50%		
Propagation Delay	$ m t_{PHL}$	0.10	0.3	0.50	μs			
Time to Low								
Output Level								
Pulse Width	PWD			0.3	μs			15
Distortion					-			
Propagation Delay	PDD	-0.35		0.35	μs		34,35	10
Difference Between	$(t_{PHL} - t_{PLH})$				•		,	
Any Two Parts								
or Channels								
Rise Time	$t_{\rm r}$		0.1		μs		23	
Fall Time	$ m t_{f}$		0.1		μs			
UVLO Turn On	${ m t_{UVLO~ON}}$		0.8		μs	$V_0 > 5 V$,	22	
Delay						$I_F = 10 \text{ mA}$		
UVLO Turn Off	$t_{ m UVLO~OFF}$		0.6		μs	$V_0 < 5 \text{ V},$		
Delay					-	$I_F = 10 \text{ mA}$		
Output High Level	$ \mathrm{CM_H} $	15	30		kV/μs	$T_A = 25$ °C,	24	11, 12
Common Mode						$I_F = 10 \text{ to } 16 \text{ mA},$		
Transient						$V_{CM} = 1500 \text{ V},$		
Immunity						$V_{CC} = 30 \text{ V}$		
Output Low Level	$ \mathrm{CM_L} $	15	30		kV/μs	$T_{A} = 25^{\circ}C,$		11, 13
Common Mode						$V_{CM} = 1500 \text{ V},$		
Transient						$V_F = 0 V$,		
Immunity						$V_{CC} = 30 \text{ V}$		

Package Characteristics (each channel, unless otherwise specified)

Parameter	Symbol	Device	Min.	Typ.*	Max.	Units	Test Conditions	Fig.	Note
Input-Output	V _{ISO}	HCPL-3150	3750			Vrms	RH < 50%,		8, 9
Momentary				-			t = 1 min.,		
Withstand Voltage**		HCPL-315J	3750				$T_A = 25^{\circ}C$		
Output-Output	V_{O-O}	HCPL-315J	1500			Vrms	RH < 50%		17
Momentary							t = 1 min.,		
Withstand Voltage**							$T_A = 25^{\circ}C$		
Resistance	R _{I-O}			10^{12}		Ω	$V_{I-O} = 500 V_{DC}$		9
(Input - Output)									
Capacitance	$C_{\text{I-O}}$	HCPL-3150		0.6		pF	f = 1 MHz		
(Input - Output)		HCPL-315J		1.3					
LED-to-Case	$\theta_{ m LC}$	HCPL-3150		391		°C/W	Thermocouple	28	18
Thermal Resistance							located at center		
LED-to-Detector	$\theta_{ m LD}$	HCPL-3150		439		°C/W	underside of		
Thermal Resistance							package		
Detector-to-Case	$\theta_{ m DC}$	HCPL-3150		119		°C/W			
Thermal Resistance									

^{*}All typical values at $T_{\!A}$ = 25 °C and $V_{\!CC}$ - $V_{\!EE}$ = 30 V, unless otherwise noted.

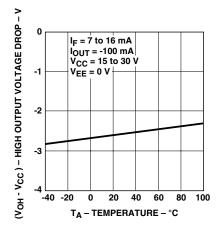
Notes:

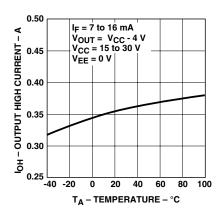
- 1. Derate linearly above 70°C free-air temperature at a rate of 0.3 mA/°C.
- $\begin{array}{l} 2. \ Maximum \ pulse \ width = 10 \ \mu s, \\ maximum \ duty \ cycle = 0.2\%. \ This \\ value \ is \ intended \ to \ allow \ for \\ component \ tolerances \ for \ designs \\ with \ I_O \ peak \ minimum = 0.5 \ A. \ See \\ Applications \ section \ for \ additional \\ details \ on \ limiting \ I_{OH} \ peak. \\ \end{array}$
- 3. Derate linearly above 70°C free-air temperature at a rate of 4.8 mW/°C.
- 4. Derate linearly above 70°C free-air temperature at a rate of 5.4 mW/°C. The maximum LED junction temperature should not exceed 125°C.
- 5. Maximum pulse width = $50 \mu s$, maximum duty cycle = 0.5%.
- 6. In this test V_{OH} is measured with a dc load current. When driving capacitive loads V_{OH} will approach V_{CC} as I_{OH} approaches zero amps.
- 7. Maximum pulse width = 1 ms, maximum duty cycle = 20%.

- 8. In accordance with UL1577, each HCPL-3150 optocoupler is proof tested by applying an insulation test voltage ≥ 4500 Vrms (≥ 5000 Vrms for the HCPL-315J) for 1 second (leakage detection current limit, $I_{I-O} \leq 5~\mu A$). This test is performed before the 100% production test for partial discharge (method b) shown in the IEC/EN/DIN EN 60747-5-2 Insulation Characteristics Table, if applicable.
- 9. Device considered a two-terminal device: pins on input side shorted together and pins on output side shorted together.
- 10. The difference between t_{PHL} and t_{PLH} between any two parts or channels under the same test condition.
- 11. Pins 1 and 4 (HCPL-3150) and pins 3 and 4 (HCPL-315J) need to be connected to LED common.
- 12. Common mode transient immunity in the high state is the maximum

- tolerable $|dV_{CM}/dt|$ of the common mode pulse, V_{CM} , to assure that the output will remain in the high state (i.e., $V_O > 15.0~V$).
- 13. Common mode transient immunity in a low state is the maximum tolerable $|dV_{CM}/dt| \ of the common mode \\ pulse, V_{CM}, to assure that the output \\ will remain in a low state (i.e., \\ V_O < 1.0 \ V).$
- 14. This load condition approximates the gate load of a 1200 V/25 A IGBT.
- 15. Pulse Width Distortion (PWD) is defined as $|t_{PHL}-t_{PLH}|$ for any given device.
- 16. Each channel.
- 17. Device considered a two terminal device: Channel one output side pins shorted together, and channel two output side pins shorted together.
- 18. See the thermal model for the HCPL-315J in the application section of this data sheet.

^{**}The Input-Output/Output-Output Momentary Withstand Voltage is a dielectric voltage rating that should not be interpreted as an input-output/output-output continuous voltage rating. For the continuous voltage rating refer to your equipment level safety specification or Agilent Application Note 1074 entitled "Optocoupler Input-Output Endurance Voltage."





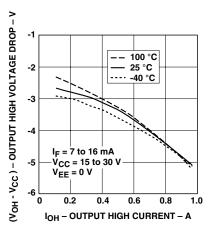
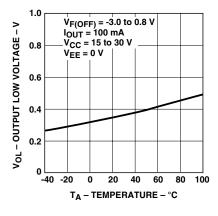
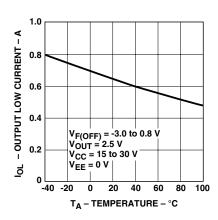


Figure 1. V_{OH} vs. Temperature.

Figure 2. $I_{\rm OH}$ vs. Temperature.

Figure 3. V_{OH} vs. I_{OH}.





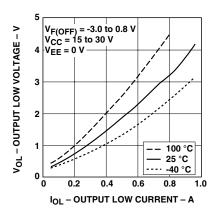
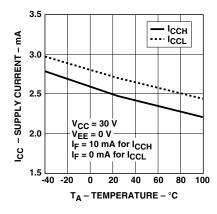
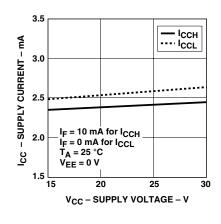


Figure 4. $V_{\rm OL}$ vs. Temperature.

Figure 5. $\rm I_{OL}$ vs. Temperature.

Figure 6. V_{OL} vs. I_{OL}.





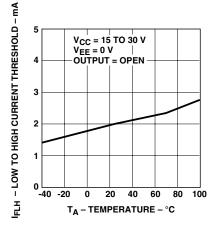
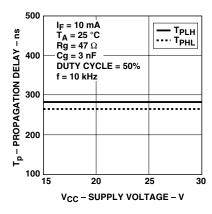
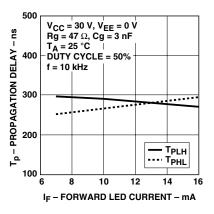


Figure 7. $I_{\rm CC}$ vs. Temperature.

Figure 8. I_{CC} vs. V_{CC} .

Figure 9. I_{FLH} vs. Temperature.





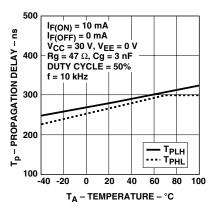
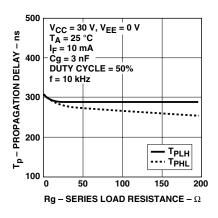
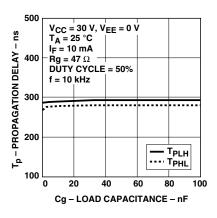


Figure 10. Propagation Delay vs. $V_{\rm CC}$.

Figure 11. Propagation Delay vs. I_F .

Figure 12. Propagation Delay vs. Temperature.





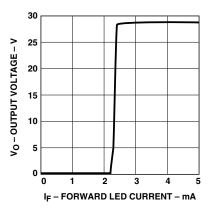


Figure 13. Propagation Delay vs. Rg.

Figure 14. Propagation Delay vs. Cg.

Figure 15. Transfer Characteristics.

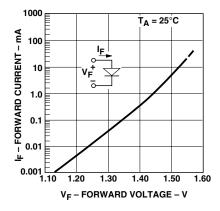
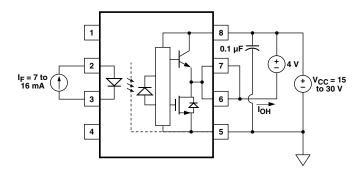


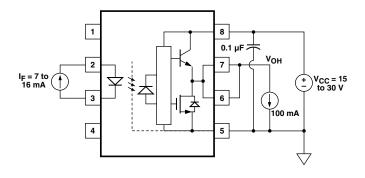
Figure 16. Input Current vs. Forward Voltage.



1 0.1 μF loL 7 + V_{CC} = 15 to 30 V

Figure 17. $I_{\rm OH}$ Test Circuit.

Figure 18. $I_{\rm OL}$ Test Circuit.



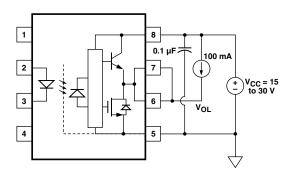
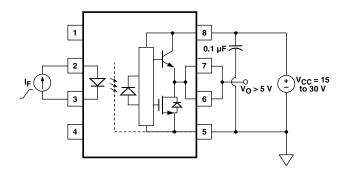


Figure 19. V_{OH} Test Circuit.

Figure 20. $V_{\rm OL}$ Test Circuit.



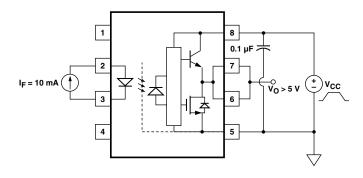
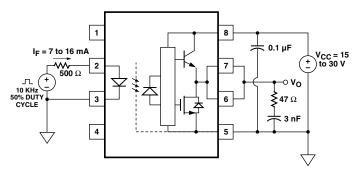


Figure 21. $I_{\rm FLH}$ Test Circuit.

Figure 22. UVLO Test Circuit.



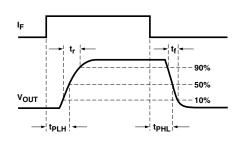
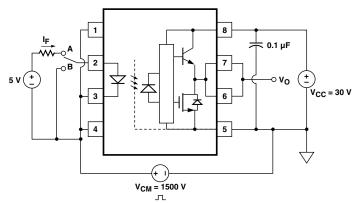


Figure 23. $t_{PLH},\,t_{PHL},\,t_{r},$ and t_{f} Test Circuit and Waveforms.



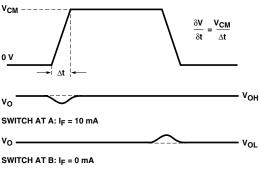


Figure 24. CMR Test Circuit and Waveforms.

Applications Information Eliminating Negative IGBT Gate Drive

To keep the IGBT firmly off, the HCPL-3150/315J has a very low maximum V_{OL} specification of 1.0 V. The HCPL-3150/315J realizes this very low V_{OL} by using a DMOS transistor with 4 Ω (typical) on resistance in its pull down circuit. When the HCPL-3150/315J is in the low state, the IGBT gate is shorted to

the emitter by Rg + 4 Ω . Minimizing Rg and the lead inductance from the HCPL-3150/315J to the IGBT gate and emitter (possibly by mounting the HCPL-3150/315J on a small PC board directly above the IGBT) can eliminate the need for negative IGBT gate drive in many applications as shown in Figure 25. Care should be taken with such a PC board design to avoid routing the IGBT collector or

emitter traces close to the HCPL-3150/315J input as this can result in unwanted coupling of transient signals into the HCPL-3150/315J and degrade performance. (If the IGBT drain must be routed near the HCPL-3150/315J input, then the LED should be reverse-biased when in the off state, to prevent the transient signals coupled from the IGBT drain from turning on the HCPL-3150/315J.)

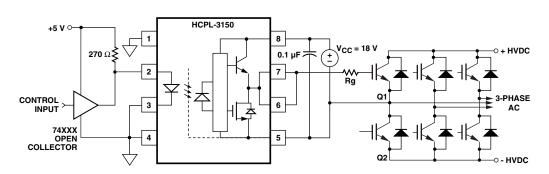


Figure 25a. Recommended LED Drive and Application Circuit.

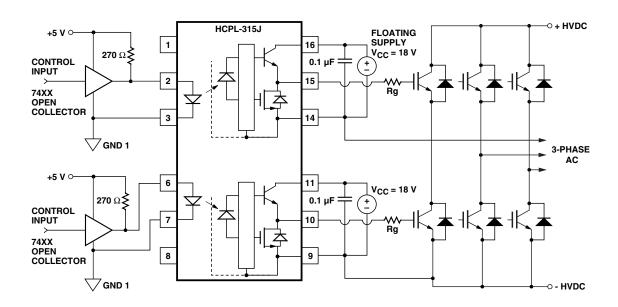


Figure 25b. Recommended LED Drive and Application Circuit (HCPL-315J).

Selecting the Gate Resistor (Rg) to Minimize IGBT Switching Losses.

Step 1: Calculate Rg Minimum From the I_{OL} Peak Specification. The IGBT and Rg in Figure 26 can be analyzed as a simple RC circuit with a voltage supplied by the HCPL-3150/315J.

$$Rg \ge \frac{(V_{CC} - V_{EE} - V_{OL})}{I_{OLPEAK}}$$

$$= \frac{(V_{CC} - V_{EE} - 1.7 V)}{I_{OLPEAK}}$$

$$= \frac{(15 V + 5 V - 1.7 V)}{0.6 A}$$

$$= 30.5 \Omega$$

The $V_{\rm OL}$ value of 2 V in the previous equation is a conservative value of $V_{\rm OL}$ at the peak current of 0.6 A (see Figure 6). At lower Rg values the voltage supplied by the HCPL-3150/315J is not an ideal voltage step. This results in lower peak currents (more margin) than predicted by this analysis. When negative gate drive is not used $V_{\rm EE}$ in the previous equation is equal to zero volts.

Step 2: Check the HCPL-3150/315J Power Dissipation and Increase Rg if Necessary. The HCPL-3150/315J total power dissipation (P_T) is equal to the

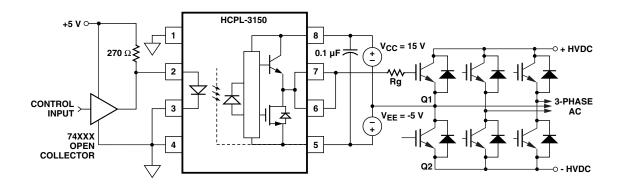
sum of the emitter power (P_E) and the output power (P_O) :

$$\begin{split} P_T &= P_E + P_O \\ P_E &= I_F \cdot V_F \cdot Duty \ Cycle \\ P_O &= P_{O(BIAS)} + P_{O \ (SWITCHING)} \\ &= I_{CC} \cdot (V_{CC} \cdot V_{EE}) \\ &+ E_{SW} (R_G, Q_G) \cdot f \end{split}$$

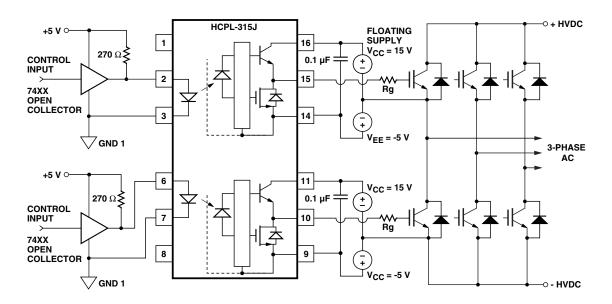
For the circuit in Figure 26 with I_F (worst case) = 16 mA, Rg = 30.5 Ω , Max Duty Cycle = 80%, Qg = 500 nC, f = 20 kHz and T_A max = 90°C:

$$P_E = 16 \, mA \cdot 1.8 \, V \cdot 0.8 = 23 \, mW$$

$$\begin{split} P_O &= 4.25 \ mA \cdot 20 \ V \\ &+ 4.0 \ \mu J \cdot 20 \ kHz \\ &= 85 \ mW + 80 \ mW \\ &= 165 \ mW \\ &> 154 \ mW \ (P_{O(MAX)} \ @ \ 90^{\circ}C \\ &= 250 \ mW - 20C \cdot 4.8 \ mW/C) \end{split}$$



 ${\bf Figure~26a.~HCPL-3150~Typical~Application~Circuit~with~Negative~IGBT~Gate~Drive.}$



 ${\bf Figure~26b.~HCPL-315J~Typical~Application~Circuit~with~Negative~IGBT~Gate~Drive.}$

PE	D
Parameter	Description
I_{F}	LED Current
V_{F}	LED On Voltage
Duty Cycle	Maximum LED
	Duty Cycle

Po Parameter	Description
I_{CC}	Supply Current
V_{CC}	Positive Supply Voltage
$ m V_{EE}$	Negative Supply Voltage
$E_{SW}(Rg,Qg)$	Energy Dissipated in the HCPL-3150/315J for
	each IGBT Switching Cycle (See Figure 27)
f	Switching Frequency

The value of 4.25 mA for I_{CC} in the previous equation was obtained by derating the I_{CC} max of 5 mA (which occurs at -40°C) to I_{CC} max at 90°C (see Figure 7).

Since P_0 for this case is greater than $P_{O(MAX)}$, Rg must be increased to reduce the HCPL-3150 power dissipation.

$$\begin{split} P_{O(SWITCHING \ MAX)} &= P_{O(MAX)} \cdot P_{O(BIAS)} \\ &= 154 \ mW \cdot 85 \ mW \\ &= 69 \ mW \\ E_{SW(MAX)} &= \frac{P_{O(SWITCHINGMAX)}}{f} \\ &= \frac{69 \ mW}{20 \ kHz} = 3.45 \ \mu J \end{split}$$

For Qg = 500 nC, from Figure 27, a value of E_{SW} = 3.45 μJ gives a Rg = 41 Ω .

Thermal Model (HCPL-3150)

The steady state thermal model for the HCPL-3150 is shown in Figure 28a. The thermal resistance values given in this model can be used to calculate the temperatures at each node for a given operating condition. As shown by the model, all heat generated flows through θ_{CA} which raises the case temperature T_{C} accordingly. The value of θ_{CA} depends on the conditions of the

board design and is, therefore, determined by the designer. The value of $\theta_{CA}=83\,^{\circ}\text{C/W}$ was obtained from thermal measurements using a 2.5 x 2.5 inch PC board, with small traces (no ground plane), a single HCPL- 3150 soldered into the center of the board and still air. The absolute maximum power dissipation derating specifications assume a θ_{CA} value of $83\,^{\circ}\text{C/W}.$

From the thermal mode in Figure 28a the LED and detector IC junction temperatures can be expressed as:

$$\begin{split} T_{JE} &= P_{E} \cdot (\theta_{LC} | | (\theta_{LD} + \theta_{DC}) + \theta_{CA}) \\ &+ P_{D} \cdot \left(\frac{\theta_{LC} \cdot \theta_{DC}}{\theta_{LC} + \theta_{DC} + \theta_{LD}} + \theta_{CA} \right) + T_{A} \end{split}$$

$$T_{JD} = P_E \left(\frac{\theta_{LC} \cdot \theta_{DC}}{\theta_{LC} + \theta_{DC} + \theta_{LD}} + \theta_{CA} \right)$$

+
$$P_D \cdot (\theta_{DC} | | (\theta_{LD} + \theta_{LC}) + \theta_{CA}) + T_A$$

Inserting the values for θ_{LC} and θ_{DC} shown in Figure 28 gives:

$$\begin{split} T_{JE} &= P_{E} \bullet (230 ^{\circ}\text{C/W} + \theta_{CA}) \\ &+ P_{D} \bullet (49 ^{\circ}\text{C/W} + \theta_{CA}) + T_{A} \\ T_{JD} &= P_{E} \bullet (49 ^{\circ}\text{C/W} + \theta_{CA}) \\ &+ P_{D} \bullet (104 ^{\circ}\text{C/W} + \theta_{CA}) + T_{A} \end{split}$$

For example, given $P_E = 45$ mW, $P_O = 250$ mW, $T_A = 70$ °C and $\theta_{CA} = 83$ °C/W:

$$T_{JE} = P_{E} \cdot 313^{\circ}\text{C/W} + P_{D} \cdot 132^{\circ}\text{C/W} + T_{A}$$

= 45 mW \cdot 313 \cdot C/W + 250 mW
\cdot 132 \cdot C/W + 70 \cdot C = 117 \cdot C

$$T_{JD} = P_E^{\bullet} 132^{\circ}\text{C/W} + P_D^{\bullet} 187^{\circ}\text{C/W} + T_A$$

= 45 mW $^{\bullet} 132\text{C/W} + 250$ mW
 $^{\bullet} 187^{\circ}\text{C/W} + 70^{\circ}\text{C} = 123^{\circ}\text{C}$

 T_{JE} and T_{JD} should be limited to 125°C based on the board layout and part placement (θ_{CA}) specific to the application.

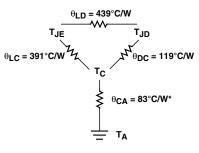


Figure 28a. Thermal Model.

 T_{JE} = LED junction temperature

 T_{JD} = detector IC junction temperature

 T_C = case temperature measured at the center of the package bottom

 θ_{LC} = LED-to-case thermal resistance

 θ_{LD} = LED-to-detector thermal resistance

 θ_{DC} = detector-to-case thermal resistance

 θ_{CA} = case-to-ambient thermal resistance

 $*\theta_{CA}$ will depend on the board design and the placement of the part.

Thermal Model Dual-Channel (SOIC-16) HCPL-315J Optoisolator

Definitions

 $\begin{array}{l} \theta_1,\,\theta_2,\,\theta_3,\,\theta_4,\,\theta_5,\,\theta_6,\,\theta_7,\,\theta_8,\,\theta_9,\\ \theta_{10} \hbox{: Thermal impedances}\\ \hbox{between nodes as shown in}\\ \hbox{Figure 28b. Ambient}\\ \hbox{Temperature: Measured}\\ \hbox{approximately 1.25 cm above the}\\ \hbox{optocoupler with no forced air.} \end{array}$

Description

This thermal model assumes that a 16-pin dual-channel (SOIC-16) optocoupler is soldered into an $8.5~\rm cm~x~8.1~cm$ printed circuit board (PCB). These optocouplers are hybrid devices with four die: two LEDs and two detectors. The temperature at the LED and the detector of the optocoupler can be calculated by using the equations below.

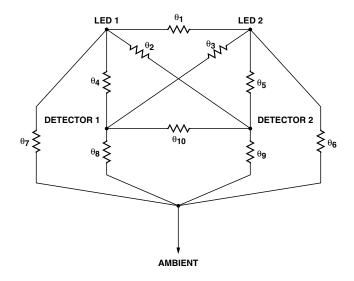


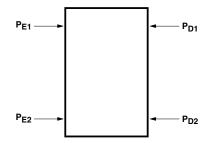
Figure 28b. Thermal Impedance Model for HCPL-315J.

$$\Delta T_{E1A} = A_{11}P_{E1} + A_{12}P_{E2} + A_{13}P_{D1} + A_{14}P_{D2}$$

$$\Delta T_{E2A} = A_{21}P_{E1} + A_{22}P_{E2} + A_{23}P_{D1} + A_{24}P_{D2}$$

$$\Delta T_{D1A} = A_{31}P_{E1} + A_{32}P_{E2} + A_{33}P_{D1} + A_{34}P_{D2}$$

$$\Delta T_{D2A} = A_{41}P_{E1} + A_{42}P_{E2} + A_{43}P_{D1} + A_{44}P_{D2}$$



where:

 ΔT_{E1A} = Temperature difference between ambient and LED 1

 ΔT_{E2A} = Temperature difference between ambient and LED 2

 ΔT_{D1A} = Temperature difference between ambient and detector 1

 ΔT_{D2A} = Temperature difference between ambient and detector 2

 P_{E1} = Power dissipation from LED 1;

 P_{E2} = Power dissipation from LED 2;

 P_{D1} = Power dissipation from detector 1;

 P_{D2} = Power dissipation from detector 2

 A_{xy} thermal coefficient (units in °C/W) is a function of thermal

impedances θ_1 through θ_{10} .

Thermal Coefficient Data (units in °C/W)

Part Number	A_{11}, A_{22}	A_{12}, A_{21}	A_{13}, A_{31}	A_{24}, A_{42}	A ₁₄ , A ₄₁	A_{23}, A_{32}	A ₃₃ , A ₄₄	A ₃₄ , A ₄₃
HCPL-315J	198	64	62	64	83	90	137	69

Note: Maximum junction temperature for above part: 125°C.

LED Drive Circuit Considerations for Ultra High CMR Performance

Without a detector shield, the dominant cause of optocoupler CMR failure is capacitive coupling from the input side of the optocoupler, through the package, to the detector IC as shown in Figure 29. The HCPL-3150/315J improves CMR performance by using a detector IC with an optically transparent Faraday shield, which diverts the capacitively coupled current away from the sensitive IC circuitry. How ever, this shield does not eliminate the capacitive coupling between the LED and optocoupler pins 5-8 as shown in Figure 30. This capacitive coupling causes perturbations in the LED current during common mode transients and becomes the major source of CMR failures for a shielded optocoupler. The main design objective of a high CMR LED drive circuit becomes keeping the LED in the proper state (on or off) during common mode transients. For example, the recommended application circuit (Figure 25), can achieve 15 kV/us CMR while minimizing component complexity.

Techniques to keep the LED in the proper state are discussed in the next two sections.

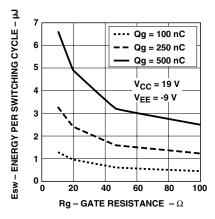


Figure 27. Energy Dissipated in the HCPL-3150 for Each IGBT Switching Cycle.

CMR with the LED On (CMR_H)

A high CMR LED drive circuit must keep the LED on during common mode transients. This is achieved by overdriving the LED current beyond the input threshold so that it is not pulled below the threshold during a transient. A minimum LED current of 10 mA provides adequate margin over the maximum $I_{\rm FLH}$ of 5 mA to achieve 15 kV/µs CMR.

CMR with the LED Off (CMR_L)

A high CMR LED drive circuit must keep the LED off $(V_F \leq V_{F(OFF)}) \mbox{ during common mode transients. For example, during a -dV_{CM}/dt transient in Figure 31, the current flowing through <math display="inline">C_{LEDP}$ also flows through the R_{SAT} and V_{SAT} of the logic gate. As long as the low state voltage developed across the

logic gate is less than $V_{F(OFF)}$, the LED will remain off and no common mode failure will occur.

The open collector drive circuit, shown in Figure 32, cannot keep the LED off during a $+ dV_{CM}/dt$ transient, since all the current flowing through C_{LEDN} must be supplied by the LED, and it is not recommended for applications requiring ultra high CMR_L performance. Figure 33 is an alternative drive circuit which, like the recommended application circuit (Figure 25), does achieve ultra high CMR performance by shunting the LED in the off state.

Under Voltage Lockout Feature

The HCPL-3150/315J contains an under voltage lockout (UVLO) feature that is designed to protect the IGBT under fault conditions which cause the HCPL-3150/315J supply voltage (equivalent to the fully-charged IGBT gate voltage) to drop below a level necessary to keep the IGBT in a low resistance state. When the HCPL-3150/315J output is in the high state and the supply voltage drops below the HCPL-3150/315J V_{UVLO-} threshold $(9.5 < V_{UVLO} < 12.0)$, the optocoupler output will go into the low state with a typical delay, UVLO Turn Off Delay, of 0.6 µs. When the HCPL-3150/315J output is in the low state and the supply voltage rises above the HCPL-3150/315J V_{UVLO+} threshold (11.0 < V_{UVLO+} < 13.5), the optocoupler will go into the

high state (assuming LED is "ON") with a typical delay, UVLO TURN On Delay, of 0.8 µs.

IPM Dead Time and Propagation Delay Specifications

The HCPL-3150/315J includes a Propagation Delay Difference (PDD) specification intended to help designers minimize "dead time" in their power inverter designs. Dead time is the time period during which both the high and low side power transistors (Q1 and Q2 in Figure 25) are off. Any overlap in Q1 and Q2 conduction will result in large currents flowing through the power devices from the high-to the low-voltage motor rails.

To minimize dead time in a given design, the turn on of LED2 should be delayed (relative to the turn off of LED1) so that under worst-case conditions, transistor Q1 has just turned off when transistor Q2 turns on, as shown in Figure 34. The amount of delay necessary to achieve this conditions is equal to the maximum value of the propagation delay difference specification, PDD $_{\rm MAX}$, which is specified to be 350 ns over the operating temperature range of -40°C to 100°C.

Delaying the LED signal by the maximum propagation delay difference ensures that the minimum dead time is zero, but it does not tell a designer what the maximum dead time will be. The maximum dead time is equivalent to the difference between the maximum and minimum propagation delay difference specifications as shown in Figure 35. The maximum dead time for the HCPL-3150/315J is 700 ns (= 350 ns - (-350 ns)) over an operating temperature range of -40°C to 100°C.

Note that the propagation delays used to calculate PDD and dead time are taken at equal temperatures and test conditions since the optocouplers under consideration are typically mounted in close proximity to each other and are switching identical IGBTs.

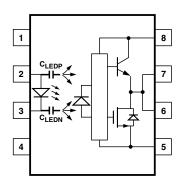


Figure 29. Optocoupler Input to Output Capacitance Model for Unshielded Optocouplers.

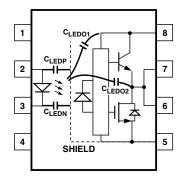


Figure 30. Optocoupler Input to Output Capacitance Model for Shielded Optocouplers.

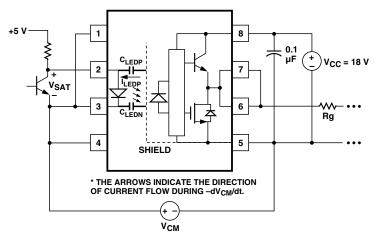


Figure 31. Equivalent Circuit for Figure 25 During Common Mode Transient.

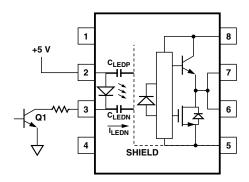


Figure 32. Not Recommended Open Collector Drive Circuit.

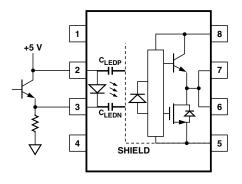
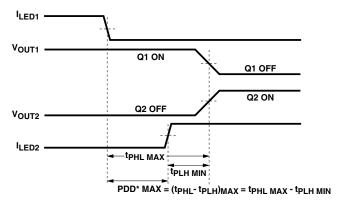
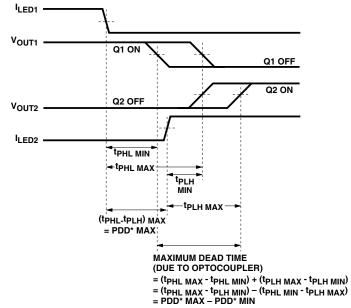


Figure 33. Recommended LED Drive Circuit for Ultra-High CMR.



*PDD = PROPAGATION DELAY DIFFERENCE NOTE: FOR PDD CALCULATIONS THE PROPAGATION DELAYS ARE TAKEN AT THE SAME TEMPERATURE AND TEST CONDITIONS.

Figure 34. Minimum LED Skew for Zero Dead Time.



*PDD = PROPAGATION DELAY DIFFERENCE NOTE: FOR DEAD TIME AND PDD CALCULATIONS ALL PROPAGATION DELAYS ARE TAKEN AT THE SAME TEMPERATURE AND TEST CONDITIONS.

Figure 35. Waveforms for Dead Time.



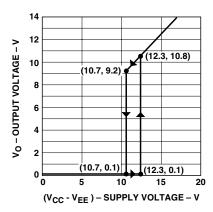


Figure 36. Under Voltage Lock Out.

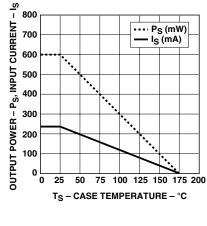


Figure 37a. HCPL-3150: Thermal Derating Curve, Dependence of Safety Limiting Value with Case Temperature per IEC/EN/DIN EN 60747-5-2.

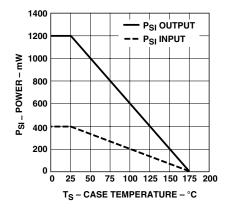


Figure 37b. HCPL-315J: Thermal Derating Curve, Dependence of Safety Limiting Value with Case Temperature per IEC/EN/DIN EN 60747-5-2.

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